

TECHNICAL DATA
DATASHEET 4765, REV. E

HERMETIC SCHOTTKY RECTIFIER

Very Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode)	120	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave (per leg)	860	A
Maximum Thermal Resistance	$R_{\theta JC}$	DC operation	0.8	°C/W
Max. Junction Temperature	T_J	-	-65 to +150	°C
Max. Storage Temperature	T_{stg}	-	-65 to +150	°C

Electrical Characteristics

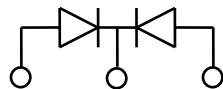
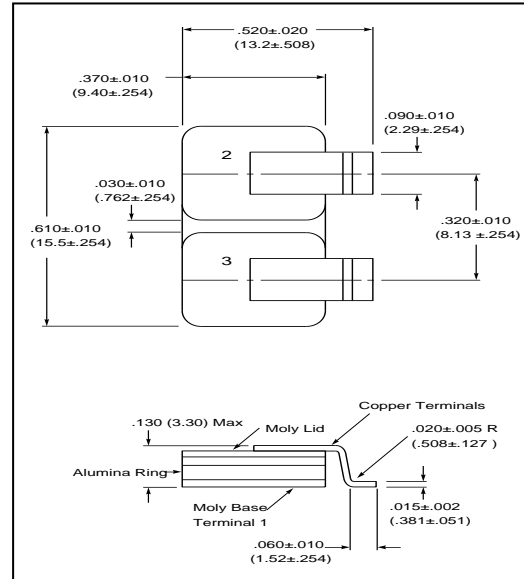
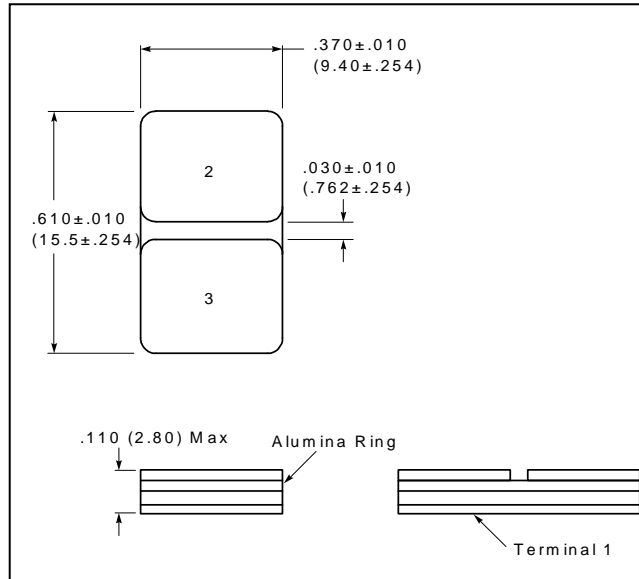
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)	V_{F1}	@ 60A, Pulse, $T_J = 25\text{ °C}$	0.70	V
	V_{F2}	@ 60A, Pulse, $T_J = 125\text{ °C}$	0.67	V
Max. Reverse Current (per leg)	I_{R1}	@ $V_R = 60V$, Pulse, $T_J = 25\text{ °C}$	6	mA
	I_{R2}	@ $V_R = 60V$, Pulse, $T_J = 125\text{ °C}$	420	mA
Max. Junction Capacitance (per leg)	C_T	@ $V_R = 5V$, $T_C = 25\text{ °C}$ $f_{SIG} = 1MHz$, $V_{SIG} = 50mV$ (p-p)	2400	pF

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
DUAL RECTIFIER, COMMON CATHODE (PB)	COMMON CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON ANODE (NB)	COMMON ANODE	CATHODE	CATHODE

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MECHANICAL DIMENSIONS: In Inches / mm

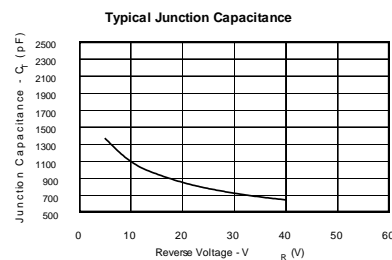
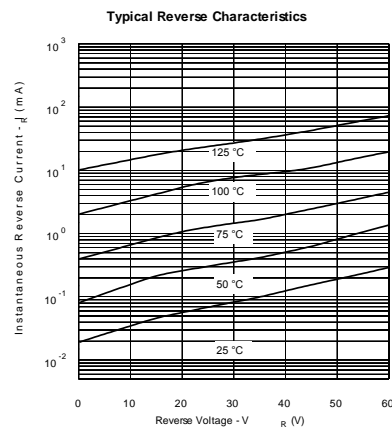
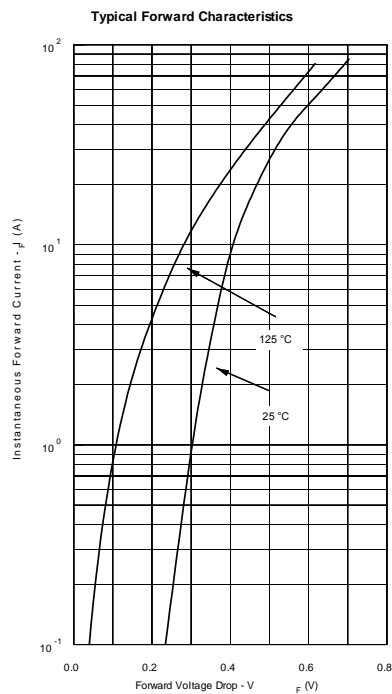


SHD-5

SHD-5B

1 2 3

Note: The V_F curves shown are for the SD200SA60 unpackaged die only.



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